

**SiC**

Silicon Carbide Diode

**5<sup>th</sup> Generation thinQ!<sup>TM</sup>**

650V SiC Schottky Diode

**IDH10G65C5**

**Final Datasheet**

Rev. 2.2, 2012-12-10

**Power Management & Multimarket**

## 5th Generation thinQ!™ SiC Schottky Diode

### IDH10G65C5

### 1 Description

ThinQ!™ Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. The Infineon proprietary diffusion soldering process, already introduced with G3 is now combined with a new, more compact design and thin-wafer technology. The result is a new family of products showing improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit ( $Q_C \times V_f$ ).

The new thinQ!™ Generation 5 has been designed to complement our 650V CoolMOS™ families: this ensures meeting the most stringent application requirements in this voltage range.

#### Features

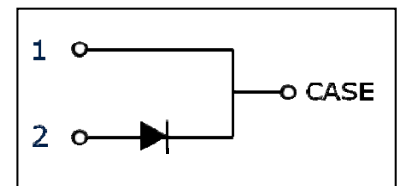
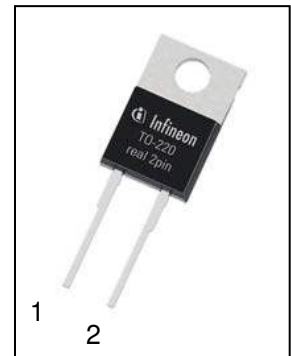
- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 22 mA<sup>2)</sup>
- Optimized for high temperature operation

#### Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

#### Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DC}$	650	V
$Q_C; V_R=400V$	15	nC
$E_C; V_R=400V$	3.4	$\mu J$
$I_F @ T_C < 140^\circ C$	10	A

**Table 2 Pin Definition**

Pin 1	Pin 2	Pin 3
C	A	n.a.

Type / ordering Code	Package	Marking	Related links
IDH10G65C5	PG-TO220-2	D1065C5	<a href="http://www.infineon.com/sic">www.infineon.com/sic</a>

1) J-STD20 and JESD22

2) All devices tested under avalanche conditions for a time periode of 10ms

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## 2 Maximum ratings

**Table 3** Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Continuous forward current	$I_F$	–	–	10	A	$T_C < 140^\circ\text{C}$ , $D=1$
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	–	–	82		$T_C = 25^\circ\text{C}$ , $t_p=10$ ms
		–	–	71		$T_C = 150^\circ\text{C}$ , $t_p=10$ ms
Non-repetitive peak forward current	$I_{F,max}$	–	–	431		$T_C = 25^\circ\text{C}$ , $t_p=10$ $\mu\text{s}$
$i^2t$ value	$\int i^2 dt$	–	–	34	A <sup>2</sup> s	$T_C = 25^\circ\text{C}$ , $t_p=10$ ms
		–	–	25		$T_C = 150^\circ\text{C}$ , $t_p=10$ ms
Repetitive peak reverse voltage	$V_{RRM}$	–	–	650	V	$T_j = 25^\circ\text{C}$
Diode dv/dt ruggedness	$dv/dt$	–	–	100	V/ns	$V_R=0..480$ V
Power dissipation	$P_{tot}$	–	–	89	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	$T_j; T_{stg}$	-55	–	175	$^\circ\text{C}$	
Mounting torque		–	–	70	Ncm	M3 screws

## 3 Thermal characteristics

**Table 4** Thermal characteristics TO-220-2

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	$R_{thJC}$	–	1.0	1.7	K/W	leaded
Thermal resistance, junction-ambient	$R_{thJA}$	–	–	62		
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	–	–	260	$^\circ\text{C}$	1.6mm (0.063 in.) from case for 10 s

## 4 Electrical characteristics

**Table 5 Static characteristics**

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	$V_{DC}$	650	–	–	V	$I_R = 0.18 \text{ mA}, T_j = 25^\circ\text{C}$
Diode forward voltage	$V_F$	–	1.5	1.7		$I_F = 10 \text{ A}, T_j = 25^\circ\text{C}$
		–	1.8	2.1		$I_F = 10 \text{ A}, T_j = 150^\circ\text{C}$
Reverse current	$I_R$	–	0.5	180	$\mu\text{A}$	$V_R = 650 \text{ V}, T_j = 25^\circ\text{C}$
		–	0.13	64		$V_R = 600 \text{ V}, T_j = 25^\circ\text{C}$
		–	2.0	1250		$V_R = 650 \text{ V}, T_j = 150^\circ\text{C}$

**Table 6 AC characteristics**

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Total capacitive charge	$Q_c$	–	15	–	nC	$V_R = 400 \text{ V}, di/dt = 200 \text{ A}/\mu\text{s}, I_F \leq I_{F,MAX}, T_j = 150^\circ\text{C}$
Total Capacitance	C	–	300	–	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
		–	40	–		$V_R = 300 \text{ V}, f = 1 \text{ MHz}$
		–	39	–		$V_R = 600 \text{ V}, f = 1 \text{ MHz}$

## 5 Electrical characteristics diagrams

Table 7

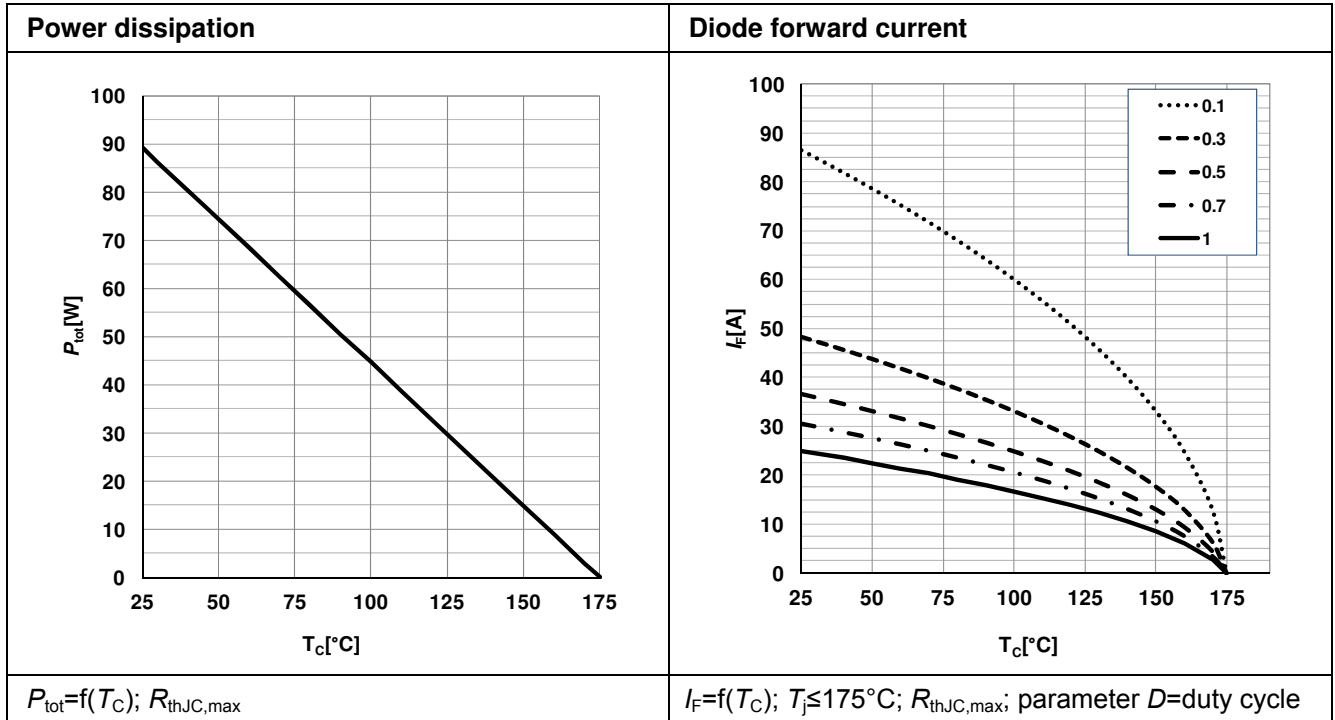
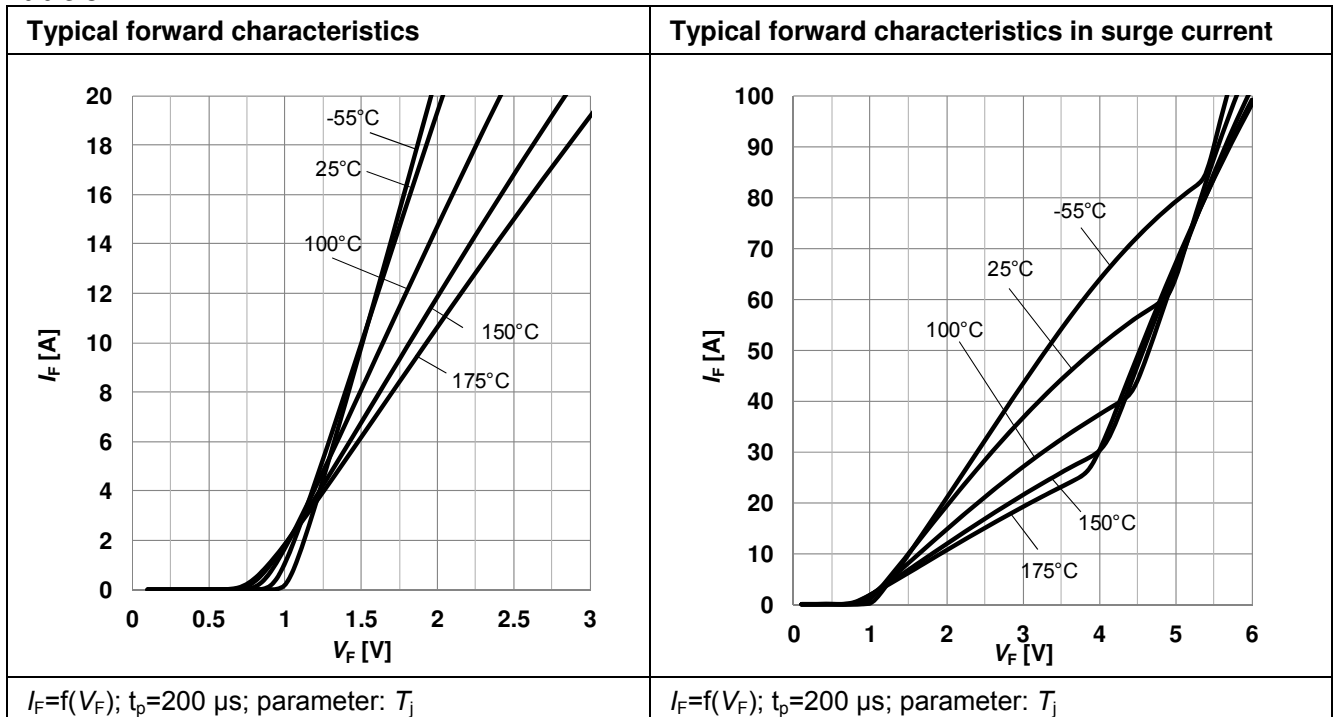
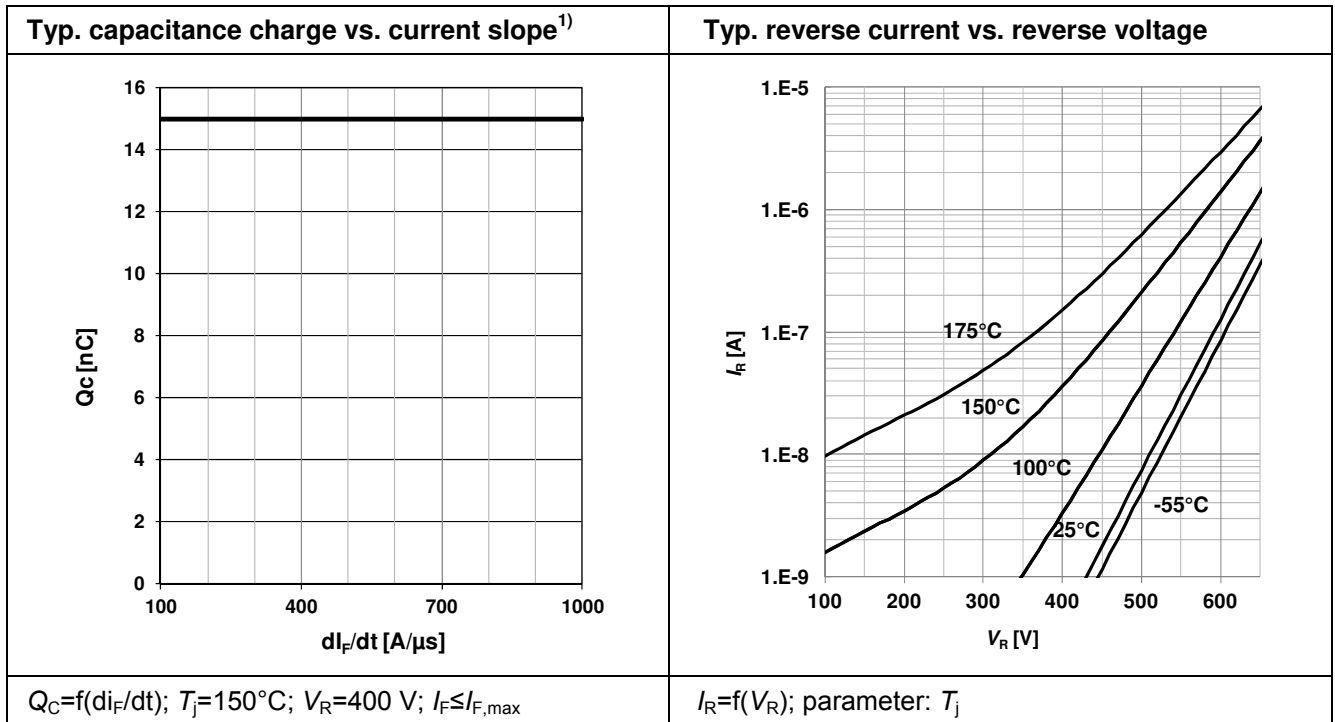


Table 8



Electrical characteristics diagrams

Table 9



1) Only capacitive charge, guaranteed by design.

Table 10

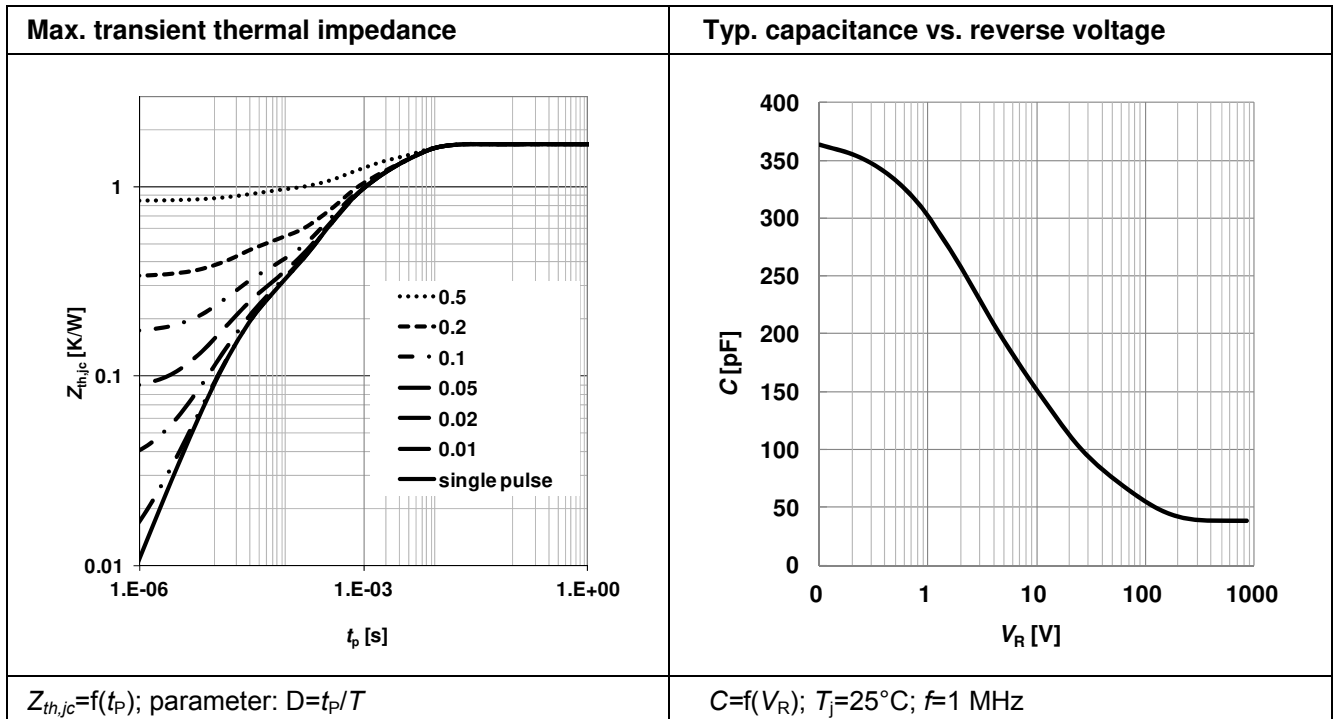
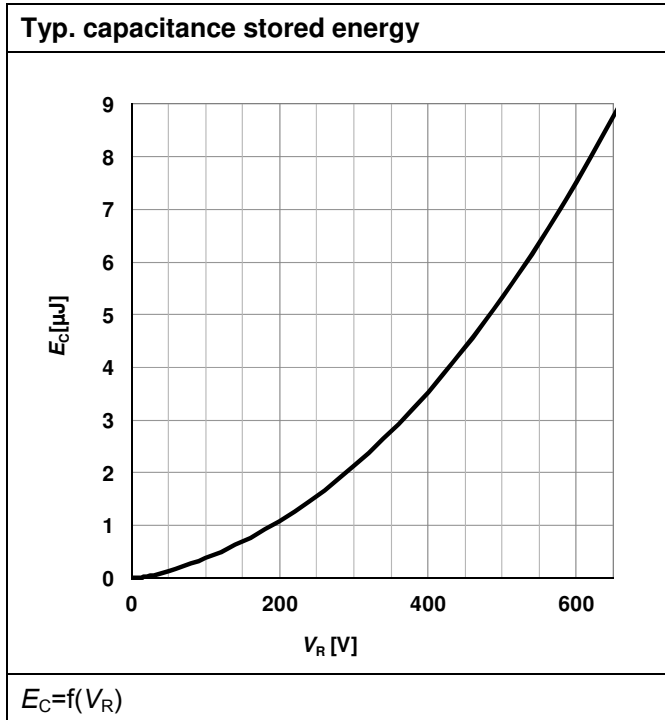


Table 11



## 6 Simplified Forward Characteristics Model

Table 12

Equivalent forward current curve	Mathematical Equation
	$V_F = V_{TH} + R_{DIFF} \cdot I_F$ $V_{TH}(T_j) = -0.001 \cdot T_j + 1.04 \text{ [V]}$ $R_{DIFF}(T_j) = 1.29 \cdot 10^{-6} \cdot T_j^2 + 1.29 \cdot 10^{-4} \cdot T_j + 0.047 \text{ [\Omega]}$
$V_F = f(I_F)$	$T_j$ in °C; $-55^\circ\text{C} < T_j < 175^\circ\text{C}$ ; $I_F < 20 \text{ A}$



7 Package outlines

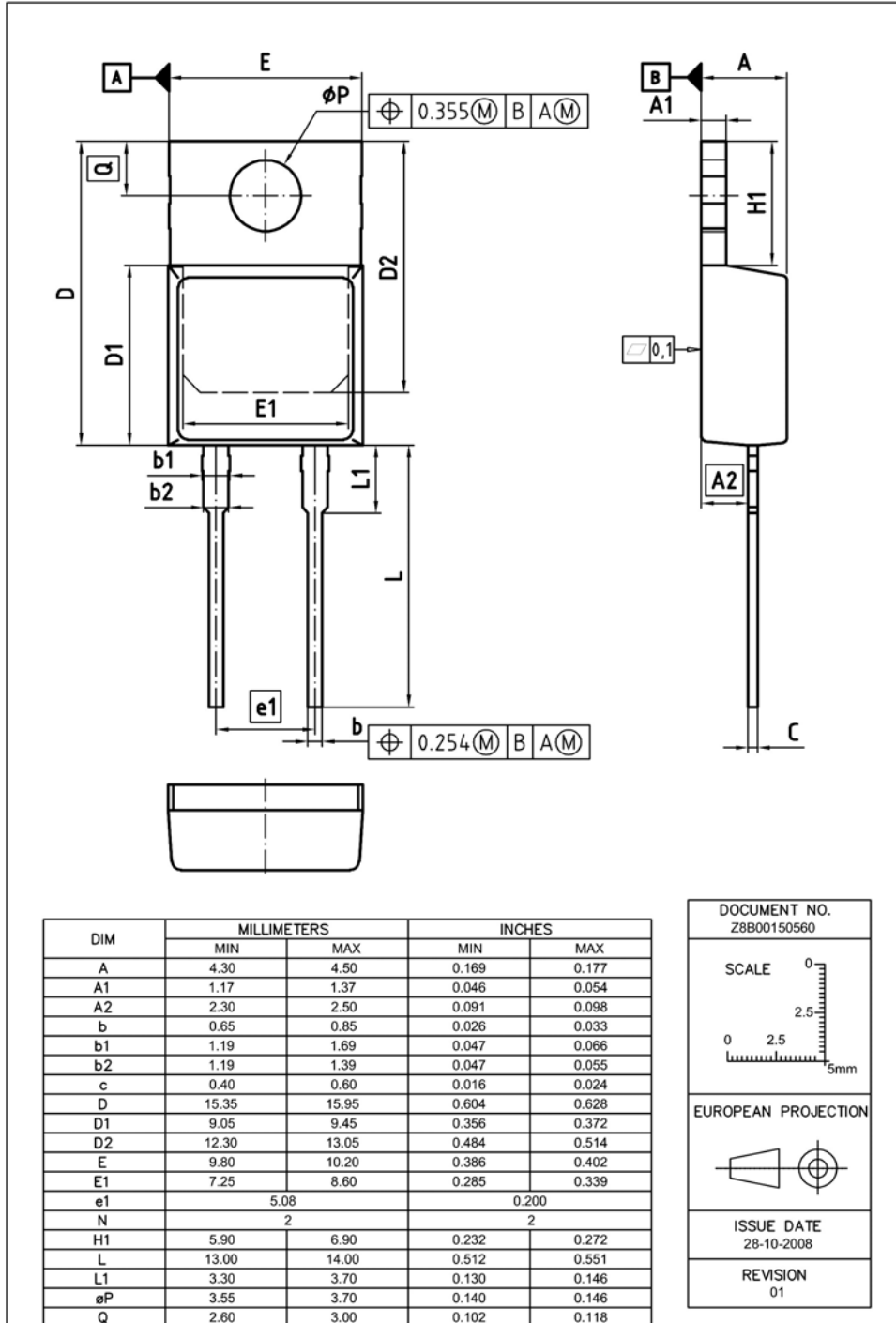


Figure 1 Outlines TO-220, dimensions in mm/inches

## 8 Revision History

### 5<sup>th</sup> Generation thinQ!™ SiC Schottky Diode

#### Revision History: 2012-12-10, Rev. 2.2

##### Previous Revision:

Revision	Subjects (major changes since last version)
2.0	Release of the final datasheet.
2.1	Reverse current values, maximum diode forward voltage.
2.2	Reverse current values, tested avalanche current, simplified calculation model

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